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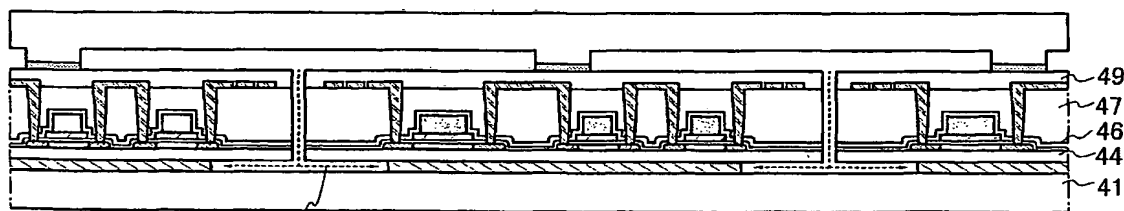
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(54) Title: METHOD FOR MANUFACTURING THIN FILM INTEGRATED CIRCUIT DEVICE, NONCONTACT THIN FILM  
INTEGRATED CIRCUIT DEVICE AND METHOD FOR MANUFACTURING THE SAME, AND IDTAG AND COIN INCLUD-  
ING THE NONCONTACT THIN FILM INTEGRATED CIRCUIT DEVICE



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(57) Abstract: To provide a thin film integrated circuit which is mass produced at low cost, a method for manufacturing a thin film  
integrated circuit according to the invention includes the steps of: forming a peel-off layer over a substrate; forming a base film over  
the peel-off layer; forming a plurality of thin film integrated circuits over the base film; forming a groove at the boundary between  
the plurality of thin film integrated circuits; and introducing a gas or a liquid containing halogen fluoride into the groove, thereby  
removing the peel-off layer; thus, the plurality of thin film integrated circuits are separated from each other.

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